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Chairs: Lin Cheng, *Cree*
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- Session 9 – Wide Bandgap IV: GaN Devices II**
- Chairs:** David Sheridan, *RFMD*
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Session 10 – Low Voltage I: Power MOSFETs

Chairs: Jun Zeng, *MaxPower Semiconductor*
Phil Rutter, *NXP*

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Session 11 – Low Voltage II: Reliability and Processing

Chairs: Yusuke Kawaguchi, *Toshiba*
Dev Alok, *Intersil*

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Chairs: Jun Cai, *Texas Instruments*

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Hong Kong University of Science and Technology

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Session 14 – Packaging and Integration I: Gate Drivers and Digital Isolators

Chairs: Kimimori Hamada, *Toyota Motor*
Katsuaki Saito, *Hitachi*

14:00

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Chairs: Reinhold Bayerer, *Infineon*
Josef Lutz, *Technical University of Chemnitz*

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